

This file lists news articles about silicon carbide (SiC) and gallium nitride (GaN) power components from the pages of <u>How2Power Today</u>. The products featured include SiC and GaN diodes, transistors, gate drivers, power modules and development boards intended for use in the design of dc-dc converters, ac-dc power supplies, and power inverters. These listings include article titles along with names, models or descriptions of products discussed in these articles. The particular newsletter issue in which an article appeared is also identified. Articles are listed in reverse chronological order so that the most recently published articles appear first.

2024:

<u>2000-V SiC Schottky Diodes Raise Efficiency For DC Link Systems</u>, Infineon Technologies' CoolSiC Schottky diode 2000-V G5 family, How2Power Today, November 2024.

<u>BMS Design Demonstrates Benefits Of Bidirectional GaN Transistor</u>, Innoscience Technology's 48-V, 180-A BMS demo, How2Power Today, November 2024.

<u>GaN Power ICs Drive Ease-Of-Use, Lower System Cost And Energy Savings</u>, Navitas Semiconductor's GaNSlim ICs, How2Power Today, November 2024.

<u>1200-V SiC MOSFETs Promise Greater Ruggedness And Reliability</u>, NoMIS Power's N3T080MP120D and N3T035MP120D SiC MOSFETs, How2Power Today, October 2024.

<u>SiC Power MOSFET Technology Is Tailored For EV Traction Inverters</u>, STMicroelectronics' fourthgeneration STPOWER silicon carbide MOSFET technology, How2Power Today, October 2024.

<u>650-V GaN Switches And Half-Bridges Feature Integrated Drivers</u>, Infineon Technologies' CoolGaN Drive product family, How2Power Today, September 2024.

<u>Reference Designs Speed SiC-Based Traction Inverter Development</u>, CISSOID's EVK-PLA1060 onboard inverter reference designs, How2Power Today, September 2024.

<u>Hybrid Si/SiC Power Modules Boost Power Density For Solar Power Generation And Energy Storage</u>, Onsemi's newest generation silicon and silicon carbide hybrid power integrated modules (PIMs) in F5BP packages, How2Power Today, September 2024.

<u>GaN IPM Enables Smaller, More Efficient High-Voltage Motors</u>, Texas Instruments' DRV7308 GaN IPM, How2Power Today, August 2024.

<u>High-Density Power Supply Reference Design Delivers 4.5 kW For AI Data Centers</u>, Navitas Semiconductor's 4.5-kW AI data center power supply reference design optimized with GaNSafe and Gen-3 "Fast" SiC power components, How2Power Today, August 2024.

<u>GaN Power IC Packages Deliver Enhanced Thermal Performance</u>, Cambridge GaN Devices' BHDFN-9-1 and DHDFN-9-1 packages, How2Power Today, July 2024.

<u>50-V GaN FET Enables High Power Density In USB-C PD Applications</u>, EPC's 50-V, 8.5-m Ω EPC2057 GaN FET, How2Power Today, July 2024.

<u>650-V SiC Diodes Address Automotive And Wider Range Of Industrial Applications</u>, Nexperia's 650-V, 10-A SiC Schottky diodes are automotive qualified (PSC1065H-Q) and available in real-two-pin DPAK packaging, How2Power Today, July 2024.

<u>Silicon And SiC MOSFETs Support High Efficiency In Data Centers</u>, onsemi's latest generation T10 PowerTrench family and EliteSiC 650-V MOSFETs, How2Power Today, July 2024.



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<u>1200-V SiC Schottky Diodes Increase Efficiency And Reliability</u>, Vishay Intertechnology's 16 Gen 3 1200-V SiC Schottky diodes featuring a merged PIN Schottky design, How2Power Today, July 2024.

<u>400-V SiC MOSFETs Benefit AI Server Power Supplies</u>, Infineon's 400-V CoolSiC MOSFETs, How2Power Today, June 2024.

<u>SiC JFET Brings Efficiency, Small Size And Robustness To Circuit Breakers</u>, Qorvo's UJ4N075004L8S SiC JFET, How2Power Today, June 2024.

<u>App Note Describes Multiphase Interleaving Of Rad-Hard Power Modules</u>, EPC Space's AN005 application note on interleaving the GaN-based FBS-GAM02 and GAM02-PSE modules for POL applications, How2Power Today, June 2024.

Known-Good-Die Screening For SiC MOSFETs, SemiQ's known-good-die (KGD) screening process and additions to QSiC family of MOSFET half-bridge modules, How2Power Today, June 2024.

GaN Power Stage IC Is Rad Hard, EPC Space's EPC7011L7SH GaN power stage, How2Power Today, May 2024.

<u>IC Drives Low-, Medium- And High-Voltage E-mode GaN HEMTs</u>, Innoscience Technology's INS1001DE driver IC, How2Power Today, May 2024.

<u>GaN Power Devices Enable Configurable, 1600-W DC-DC Solution For Space</u>, VPT's SGRBX dc-dc converter box, How2Power Today, April 2024.

<u>2000-V SiC MOSFETs Support Higher DC Link Voltages</u>, Infineon Technologies' 2000-V CoolSiC MOSFETs, How2Power Today, April 2024.

<u>GaN Reliability Report Adds Overvoltage Guidelines, Information On Thermomechanical Wearout,</u> EPC's Phase-16 Reliability Report, How2Power Today, April 2024.

<u>750-V SiC MOSFETs Enhance Performance Of Industrial And Automotive Applications</u>, Infineon Technologies' 750-V G1 discrete CoolSiC MOSFETs, How2Power Today, April 2024.

<u>APEC 2024 Highlights WBG Progress, Power Challenges In AI And Beyond</u>, Article reports on Qorvo's 1200-V SiC Modules, Microchip Technology's 3.3-kV XIFM mSiC gate driver, Cambridge GaN Devices' ICeGaN reference designs and demos, Texas Instruments' LMG2100R044 and LMG3100R017 100-V GaN power stages, Analog Devices' LT8418 100-V half-bridge GaN driver, and other GaN and SiC news, How2Power Today, March 2024.

GaN FET Features 1-mΩ On-Resistance, EPC's EPC2361GaN FET, How2Power Today, March 2024.

<u>Switcher ICs Improve Efficiency For Multi-Output Power Supplies</u>, Power Integrations' InnoMux-2 power-supply ICs featuring 750-V PowiGaN switches, How2Power Today, March 2024.

<u>Sic MOSFET Modules In Full-Bridge Configurations Delivery High Efficiency And Reliability</u>, SemiQ's QSiC 1200-V SiC MOSFET modules, How2Power Today, March 2024.



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<u>Offline Switcher ICs Enable Design Of Highly Efficient, Compact USB PD Adapters</u>, Power Integrations' InnoSwitch5-Pro switcher ICs featuring 750-V or 900-V PowiGaN switches, How2Power Today, February 2024.

<u>Fast-Switching GaN FETs Enable 75- To 231-A Laser Diode Control For Automotive LiDAR</u>, EPC's EPC9179, EPC9181, and EPC9180 evaluation boards featuring pulse-current laser drivers, How2Power Today, February 2024.

<u>100-V Bidirectional GaN IC For 48-V And 60-V Battery Management Systems</u>, Innoscience Technology's INV100FQ030A member of the company's VGaN IC family, How2Power Today, February 2024.

<u>1200-V SiC MOSFETs Target Industrial Applications</u>, Nexperia's NSF040120L3A0 and NSF080120L3A0 SiC MOSFETs, How2Power Today, February 2024.

<u>SPICE Library Adds SiC Power Devices And IGBTs</u>, ROHM Semiconductor's expanded SPICE model lineup, How2Power Today, January 2024.

<u>SiC MOSFET Half-Bridge Modules Are Engineered For Reliability</u>, SemiQ's GCMX010A120B2B1P and other SiC MOSFET modules, How2Power Today, January 2024.

<u>SiC MOSFET Half-Bridge Module Is Hermetically Sealed</u>, Solitron Devices' SD11487 SiC power module, How2Power Today, January 2024.

Low-Voltage HEMTs Come In Easy-To-Use Flip-Chip QFNs, Innoscience Technology's INN040FQ043A, INN100FQ016A, INN100FQ025A, INN150FQ032A, and INN150FQ070A GaN HEMTs, How2Power Today, January 2024.

GaN FETs With Integrated Gate Drivers Shrink AC-DC Adapters, Texas Instruments' LMG3622, LMG3624 and LMG3626 GaN FETs, How2Power Today, January 2024.

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<u>62-mm Package For SiC MOSFETs Enables Higher Efficiency And Power Density</u>, Infineon Technologies' CoolSiC MOSFET modules, How2Power Today, December 2023.

<u>650-V GaN Power Switch Integrates Lossless Current Sensing</u>, GaNPower International's GPI65060DFC power switch, How2Power Today, December 2023.

<u>1200-V SOT-227 SiC MOSFET Modules Are Designed For High Reliability</u>, SemiQ's QSiC silicon carbide modules, How2Power Today, December 2023.

<u>Semiconductor Technology Pushes Silicon Beyond Its Assumed Limits For Power Devices</u>, iDEAL Semiconductor's SuperQ technology, *Technology enables silicon power switches to compete with SiC and GaN*, How2Power Today, November 2023.

Switcher ICs Feature 1250-V GaN Switch, Power Integrations' InnoSwitch3-EP 1250-V ICs, , How2Power Today, November 2023.



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<u>GaN-Based Reference Design Shrinks Motor Drives For eBikes</u>, Robots And Drones, EPC's EPC9194 motor drive inverter reference design, How2Power Today, November 2023.

<u>Robust Integrated GaN Platform Is Optimized For High-Power Applications</u>, Navitas Semiconductor's GaNSafe Power ICs, How2Power Today, October 2023.

<u>40-V Rad-Hard GaN FETs Deliver High Performance For LEO And GEO Applications</u>, EPC's EPC7001 and EPC7002 rad-hard GaN FETs, How2Power Today, August 2023.

<u>GaN Driver Integrates Galvanic Isolation For Power Rails Up To 1700 V</u>, STMicroelectronics' STGAP2GS gate driver, How2Power Today, July 2023.

<u>SiC Trench MOSFETs In TO263-7 Boost E-Mobility</u>, Infineon's 1200-V CoolSiC MOSFETs, How2Power Today, July 2023.

<u>SiC Schottky Diodes Offer 650-V To 1200-V And 6-A To 10-A Ratings</u>, Bourns' BSDH10G65E2, BSDH10G120E2, BSDD06G65E2, BSDL10S65E6, BSDW20S65C6, BSDW20G120C2SiC Schottky barrier diodes, How2Power Today, July 2023.

<u>700-V SiC MOSFET Is Military Grade</u>, Solitron Devices' SD11710 SiC MOSFET in a hermetically sealed TO-258, How2Power Today, July 2023.

<u>SiC Gate Driver Improves Efficiency, Simplifies Design For EV Traction Inverters</u>, Texas Instruments' UCC5880-Q1 isolated gate driver, How2Power Today, June 2023.

GaN ICs Are Robust And Easy To Use, Cambridge GaN Devices' H2 series ICeGaN HEMTs, How2Power Today, June 2023.

<u>GaN Transistors Expand 100-V And 200-V Rad Hard Options</u>, EPC's EPC7020 200-V, 11-m Ω GaN FET and EPC7003 100-V, 30-m Ω GaN FET, How2Power Today, June 2023.

<u>SiC E-Fuse Demonstrator Eases Design Of Solid-State Power Protection</u>, Microchip Technology's SiCbased E-fuse demonstrator board, How2Power Today, June 2023.

<u>E-Mode GAN FETs Address Low- And High-Voltage Applications</u>, Nexperia's GAN080-650EBE, GAN140-650EBE, GAN140-650EBE, and GAN190-650FBE 650-V, GaN FETs in DFNs; GAN3R2-100CBE 100-V GaN FET in a WLCSP; and GAN7R0-150LBE 150-V GaN FET in an LGA, How2Power Today, June 2023.

<u>1200-V SiC Power Modules Provide Independent Outputs And Small Size</u>, Solitron Devices' SD11911 and SD11912 1200-V SiC power modules, How2Power Today, June 2023.

<u>GaN FETs Plus Controller Build High-Density Buck Converter Reference Design</u>, EPC's EPC9158 synchronous buck reference design board, How2Power Today, May 2023.

<u>Merged PiN Schottky Structure Enhances Robustness Of 650-V SiC Diodes</u>, Nexperia's PSC1065K 10-A, 650-V SiC Schottky diode, How2Power Today, May 2023.



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<u>900-V Switcher ICs Benefit EV And Industrial Applications</u>, Power Integrations' 900-V InnoSwitch3 flyback switcher ICs, How2Power Today, April 2023.

<u>SiC FET In TOLL Package Offers Higher Voltage Rating</u>, Lower On-Resistance, Qorvo's UJ4SC075005L8S SiC FET, How2Power Today, April 2023.

<u>Simulation Tools For SiC Devices Improve Accuracy For Soft Switching</u>, onsemi's online Elite Power Simulator and Self-Service PLECS Model Generator, How2Power Today, April 2023.

<u>Reliability Report Projects GaN Device Lifetime In Real-World Applications</u>, EPC's Phase-15 Reliability Report, How2Power Today, April 2023.

<u>Simulator Eases Evaluation Of SiC Power Solutions</u>, Microchip Technology's MPLAB SiC Power Simulator, How2Power Today, April 2023.

Integrated 100-V GaN Half-Bridge With Driver Saves Board Space, Innoscience Technology's ISG3201 SolidGaN half-bridge, How2Power Today, April 2023.

<u>High-Performance Vertical GaN Semiconductors Will Begin Production In Q3</u>, NexGen Power Systems' 700-V and 1200-V NexGen Vertical GaN semiconductor devices, How2Power Today, March 2023 issue.

<u>900-V GaN Power ICs Feature Low On-Resistance And Low Leakage</u>, GaNPower International's GPI4TIC15DFV and GPI6TIC15DFV GaN ICs, How2Power Today, January 2023 issue.

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<u>PFC And Hybrid-Flyback IC Drives Performance In GaN-Based USB-C Adapters</u>, Infineon Technologies' XDPS2221 controller IC for USB-PD, How2Power Today, December 2022 issue.

Easy-To-Use GaN HEMTs Are Available In High Volume, Cambridge GaN Devices' IceGaN smart HEMT, monolithically integrated power solutions, How2Power Today, December 2022 issue.

<u>Next-Generation GaN Technology Doubles Power Density</u>, Efficient Power Conversion's EPC2619 80-V $4-m\Omega$ GaN FET, How2Power Today, November 2022 issue.

<u>1-kV Voltage Sensor Measures VDS Of SiC And GaN Transistors</u>, Tell-i Technologies' VON1k5Vm sensor, How2Power Today, November 2022 issue.

<u>Gan HEMT Family Adds 190-m Ω , 350-m Ω And 600-m Ω Devices In DFN Packages, Innoscience Technology's INN650D190A, INN650DA190A, INN650D350A, INN650DA350A and INN650DA600A 650-V Gan HEMT devices, How2Power Today, November 2022 issue.</u>

<u>GaN Half-Bridge Power ICs Enable Megahertz Switching</u>, Navitas Semiconductor's NV6247 and NV6245C GaNSense half-bridge ICs, How2Power Today, October 2022 issue.



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NSREC Notes: Exhibitors Showcase Latest Reference Designs Along With Progress In Rad-Tolerant And Rad-Hard Power Components, mentions EPC Space's EPC7C006 reference design demo board for a rad-hard three-phase motor control plus driver with GaN FETs and the FBS-GAM02-P-R50 motor drive module in a reaction wheel application example; and Apogee Semiconductor's AFP1422 rad-hard PWM controller IC for GaN power switches, How2Power Today, September 2022 issue.

<u>Power Modules Simplify SiC Inverter Designs</u>, STMicroelectronics' A2F12M12W2-F1 and A2U12M12W2-F2 STPOWER modules, How2Power Today, September 2022 issue.

<u>App Note Describes Efficient Power Supply For Three-Phase Smart Utility Meters</u>, GaNPower International's GPI-HVACDC-QR-EVB eval board and application note, How2Power Today, August 2022 issue.

<u>750-V SiC FETs Come In Thermally Enhanced Surface-Mount D2PAKs</u>, Qorvo's Gen 4 UJ4C/SC series SiC FETs with 9- to $60-m\Omega$ on-resistance, How2Power Today, August 2022 issue.

<u>Test Kits With Cooling Speed Evaluation Of SiC-Based Inverter Designs</u>, PPM Power's inverter test kits, How2Power Today, July 2022 issue.

<u>Rad Hard 100-V GaN Transistor Boasts Low On-Resistance</u>, Efficient Power Conversion's EPC7018 3.9- $m\Omega$, 345-Apulsed GaN FET, How2Power Today, July 2022 issue.

<u>GaN Transistor Targets Consumer, Industrial and Data Center Applications</u>, GaN Systems' GS-065-018-2-L 650-V 78-mΩ GaN transistor, How2Power Today, July 2022 issue.

<u>Companies Co-develop Three-Phase SiC Power Stack</u>; CISSOID, NAC Group and Advanced Conversion collaborate on SiC power stack, How2Power Today, July 2022 issue.

<u>GaN-Based Inverter Reference Design Shrinks Motor Drives For eBikes And Drones</u>, EPC's EPC9173 GaN-based inverter reference design, How2Power Today, June 2022 issue.

<u>65-W ACF Reference Design Achieves 30-W/in3 Power Density</u>, Innoscience Technology and Silanna Semiconductor's 65-W active clamp flyback (AFC) reference design, How2Power Today, June 2022 issue.

Switcher ICs Extend Adapter Designs To 220 W With Small Size, Power Integrations' InnoSwitch4-CZ and the ClampZero ICs, How2Power Today, June 2022

<u>350-V GaN Transistor Boasts Small Size And Low Cost</u>, Efficient Power Conversion's EPC2050 350-V GaN transistor, How2Power Today, May 2022 issue.

<u>1200-V SiC FETs Ease Design Optimization</u>, UnitedSiC's UF4SC120023K4S, UF4SC120030K4S, UF4C120053K4S/K3S and UF4C120070K4S/K3S Gen 4 1200-V SiC FETs, How2Power Today, May 2022 issue.

<u>1200-V SiC MOSFET Chips Improve On-Resistance And Robustness</u>, Infineon Technologies' CoolSiC MOSFET 1200-V M1H advanced SiC chip, How2Power Today, May 2022 issue.



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<u>Demos Showcase GaN Devices In Range of Topologies And Power Levels</u>, Tagore Technology's APEC 2022 demos including a 65-W quasi-resonant flyback, a 240-W totem-pole PFC + LLC demo, a half-bridge GaN evaluation board, and an 800-W phase-shifted full-bridge reference design, How2Power Today, May 2022 issue.

<u>Highly Accurate Measurement System For GaN And SiC Semiconductors</u>, Teledyne LeCroy's DL-ISO high-voltage optically isolated 1-GHz probe and Power-Device test software, How2Power Today, May 2022 issue.

<u>GaN IC Enables Fast Switching, Narrow Pulses For Automotive Lidar</u>, Efficient Power Conversion's EPC2221 common-source dual GaN FET, How2Power Today, May 2022 issue.

Low-Cost 1200-V SiC MOSFET Offers 50-mΩ On-Resistance, Solitron Devices' SD11720 SiC MOSFET, How2Power Today, May 2022 issue.

APEC 2022: GaN Power Devices And Advanced Topologies Are Put To Work In Latest Adapter Designs, Infineon's 240-W technology demonstrator, Innoscience Technology's 140-W USB-PD 3.1 adapter and 240-W adapter demos, Efficient Power Conversion's EPC9171 240-W USB-PD 3.1 fast charger reference design, Silanna Semiconductor's RD-16 100-W 2C1A multi-port USB-PD reference design and RD-25 118-W 1C1A multi-port USB-PD reference design, Power Integrations' HiperPFS-5 family of quasi-resonant PFC ICs with a 750-V GaN switch, and DER-916 reference design for a Multi-Port USB-C Wall Outlet Without Buck Converters, How2Power Today, April 2022 issue.

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<u>Startup's 650-V GaN Devices' Boast Ease Of Use</u>, Cambridge GaN Devices' ICeGaN 650-V H1 series of GaN HEMTs, How2Power Today, April 2022 issue.

<u>GaN HEMT Enables High-Efficiency Power Supply For Smart Utility Meters</u>, GaNPower International's application note on high-voltage GaN for smart utility meters, How2Power Today, April 2022 issue.

<u>140-W Adapter Demo Uses Both High- And Low-Voltage GaN Switches</u>, Innoscience Technology's 140-W power supply demo, How2Power Today, April 2022 issue.

<u>Quasi-Resonant PFC Chips With GaN Switch Shrink PFC Stage For Adapters</u>, Power Integrations' HiperPFS-5 family of power-factor-correction ICs, How2Power Today, April 2022 issue.

<u>3.3-kV SiC MOSFETs And SBDs Extend Design Options For HV Power Electronics</u>, Microchip Technology's expanded SiC portfolio includes the 25-m Ω MSC025SMA330 SiC MOSFET and 90-A MSC090SDA330 SiC SBD, How2Power Today, April 2022 issue.

<u>150-V GaN HEMTs Feature 8-V Withstand Gate Voltage</u>, ROHM Semiconductor's GNE10xxTB series GaN HEMTs, How2Power Today, April 2022 issue.



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<u>40-V Bidirectional GaN HEMT Brings GaN Into Phone Handsets</u>, Innoscience Technology's INN40W08 GaN-on-Si e-mode HEMT, How2Power Today, March 2022 issue.

<u>Inverter Reference Design Delivers Premium Motor Performance At Low Cost</u>, Efficient Power Conversion's EPC9167 inverter reference design, How2Power Today, March 2022 issue.

<u>A 2-kW Bidirectional Converter Reference Design Board With High Efficiency</u>, Efficient Power Conversion's EPC9170 demo board, How2Power Today, February 2022 issue.

<u>Switcher ICs With 1700-V SiC MOSFET Simplify EV Power Supply Design</u>, Power Integrations' INN3947CQ-TL and INN3949CQ-TL power supply ICs, How2Power Today, February 2022 issue.

<u>Demo Boards Ease Transition From Rad Hard Si MOSFETs To GaN Devices</u>, EPC Space's EPC7C001, EPC7C002, EPC7C003 low-side driver demo boards, EPC7C005 half-bridge output demo board, and EPC7C006 three-phase motor demo board, How2Power Today, February 2022 issue.

<u>Dual Gate Drivers For SiC And IGBT Switching</u>, STMicroelectronics' dual-channel galvanically-isolated gate drivers for IGBTs (STGAP2HD) and SiC MOSFETs (STGAP2SICD), How2Power Today, February 2022 issue.

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<u>Third-Gen SiC MOSFETs Enhance Performance For EVs</u>, STMicroelectronics' third-generation STPOWER SiC MOSFETs, How2Power Today, January 2022 issue.

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<u>SiC Power Stage Reference Design Accelerates Inverter Development</u>, Mersen's 150-kVA three-phase SiC Power Stack reference design developed in collaboration with Microchip Technology, How2Power Today, December 2021 issue.

<u>GaN Power ICs Integrate Fast Overcurrent And Overtemperature Protection</u>, Navitas Semiconductor's third-gen GaNFast power ICs, How2Power Today, November 2021 issue.

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<u>1200-V SiC Half-Bridge Power Modules Target Avionics Applications</u>, Solitron Devices' SD11900 SiC Power Modules, How2Power Today, October 2021 issue.

GaN Gate Driver Boosts Speed, Flexibility In Industrial And Home Automation, STMicroelectronics' STDRIVEG600 half-bridge gate driver, How2Power Today, October 2021 issue.

<u>750-V SiC FETs Boast A Low On-Resistance Of 6 m Ω </u>, United SiC's Gen 4 750-V SiC FETs, How2Power Today, September 2021 issue.



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<u>650-V GaN FET Features Integrated Driver And Enhanced Protection</u>, Tagore Technology's TP44200NM 180-m Ω 650-V GaN E-HEMT device, How2Power Today, August 2021 issue.

<u>MOSFET Dies, Discretes And Power Modules Are Offered With 1700-V Rating</u>, Microchip Technology's expanded SiC portfolio, How2Power Today, August 2021 issue.

Bus Converter Reference Design Packs 1 kW Into Eighth-Brick Footprint, Efficient Power Conversions' EPC9149 reference design and demo board, How2Power Today, July 2021 issue.

<u>Totem-Pole PFC Controller Provides High Performance, Cost Effective Design</u>, ON Semiconductor's NCP1680 CrM PFC controller IC, How2Power Today, July 2021 issue.

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<u>1200-V Silicon Carbide MOSFET Aims To Replace Silicon Devices</u>, Cree's CMF20120D 1200-V SiC MOSFET, How2Power Today, January 2011 issue.

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<u>SiC Schottkys Push Voltage Ratings to 1700 V</u>, Cree's CPW3-1700S010B and CPW3-1700S025B 1700-V SiC Schottky diodes, How2Power Today, April 2010 issue.

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<u>GaN-Based Power Stages Look To Reshape Point-of-Load Landscape</u>, International Rectifier's GaN iP2010 and iP2011 integrated power stages, How2Power Today, March 2010 issue.

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